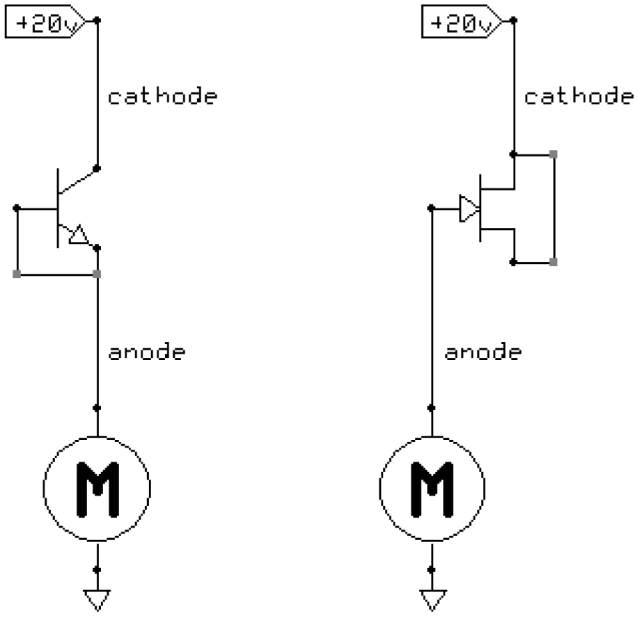
Reverse leakage of diode-connected BJTs and JFETs

All were measured at 20vDC reverse voltage at 25°C
Values are approximate due to the very low currents

PN4117A	~ 1 pA	low-current, low-leakage FET
MPSH10	~ 5 pA	mid-RF transistor
2N5179	~ 5 pA	mid-RF transistor
2SD786	~ 15 pA	ultra-low voltage noise transistor
J111	~ 20 pA	medium-high current switching FET
2N5550	~ 30 pA	high-voltage small-signal transistor
2N3904	~ 50 pA	small-signal DC to low-RF transistor
1N3595	~ 200 pA	low-leakage signal diode (silicon)
1N4148	~ 6,000 pA (6 nA)	general-purpose signal diode (silicon)

JFETS were measured from Gate (anode) to Drain + Source (cathode);
BJTs were measured from Base + Emitter (anode) to Collector (cathode):



Leaving the BJT emitters floating did not significantly improve leakage.